



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

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Application Number

10/604,478

Applicant(s)

Gabillard, et al.

Filing Date

7/24/03

Group Art Unit

2817

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		4,956,615	9/11/90	Böhme, et al.	330	288	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
W		EP 0558 244 A1	22.02.93	EUROPE	—	—		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

W		"Tunable Linearity Characteristics of a DC-3 GHz InP HBT Active Feedback Amplifier", Kobayashi, et al., IEEE, October 1999, pp. 291-294
W		High-Bit-rate, High-Input-Sensitivity Decision Circuit Using Si Bipolar Technology" by K. Ishii et al, IEEE Journal of Solid-State Circuits, vol 29, No 5, May 1994, pp. 546-549

EXAMINER

NGUYEN, KV

DATE CONSIDERED

11/15/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.